TECHNICAL DATA
DATA SHEET 4067, REV B

HERMETIC POWER MOSFET
N-CHANNEL

FEATURES:

- **30 Volt, 0.019 Ohm MOSFET**
- **Hermetically Sealed**
- **Add a "C" after the SHD for ceramic seals (SHDC220212)**
- **Surface Mount Package**

MAXIMUM RATINGS

ALL RATINGS ARE AT T_A = 25°C UNLESS OTHERWISE SPECIFIED.

GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
CONTINUOUS DRAIN CURRENT V_{GS} = 10V, T_C = 25°C V_{GS} = 10V, T_C = 100°C	I_D	-	-	13 9	Amps
PULSED DRAIN CURRENT @ T_C = 25°C	I_{DM}	-	-	40	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
THERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	1.7	°C/W
TOTAL DEVICE DISSIPATION @ T_C = 25°C	P_D	-	-	75	Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE V_{GS} = 0V, I_D = 250 μA	BV_{DSS}	30	-	-	Volts
DRAIN TO SOURCE ON STATE RESISTANCE V_{GS} = 10V, I_D = 7.3A V_{GS} = 4.5V, I_D = 3.7A	$R_{DS(ON)}$	-	-	 0.019 0.030	Ω
GATE THRESHOLD VOLTAGE V_{DS} = V_{GS}, I_D = 250μA	$V_{GS(th)}$	1.0	-	3.0	Volts
ZERO GATE VOLTAGE DRAIN CURRENT, T_J = 25°C (V_{DS} = 30V, V_{GS} = 0V), T_J = 125°C	I_{DSS}	-	-	25 250	μA
GATE TO SOURCE LEAKAGE FORWARD V_{GS} = 16V GATE TO SOURCE LEAKAGE REVERSE V_{GS} = -16V	I_{GSS}	-	-	100 -100	nA
TOTAL GATE CHARGE V_{GS} = 10V, GATE TO SOURCE CHARGE V_{DS} = 24V, GATE TO DRAIN CHARGE I_D = 7.3A	Q_g Q_{gs} Q_{gd}	-	-	80 20 23	nC
TURN ON DELAY TIME V_{DD} = 15V, RISE TIME I_D = 7.3A, TURN OFF DELAY TIME R_G = 6.2Ω, FALL TIME V_{GS} = 10V	$t_{d(ON)}$ t_r $t_{d(OFF)}$ t_f	-	20 80 80 80	-	nsec
DIODE FORWARD VOLTAGE T_J = 25°C, I_S = 7.3A V_{GS} = 0V	V_{SD}	-	-	1.0	Volts
REVERSE RECOVERY TIME T_J = 25°C, I_S = 7.3A, di/dt = 100A/μsec, REVERSE RECOVERY CHARGE V_{DD} = 25V	t_{rr} Q_{rr}	- -	110 300	- -	nsec μC
INPUT CAPACITANCE V_{GS} = 0V, V_{DS} = 25V, OUTPUT CAPACITANCE f = 1MHz REVERSE TRANSFER CAPACITANCE	C_{iss} C_{oss} C_{rss}	-	1640 660 220	-	pF

SENSITRON

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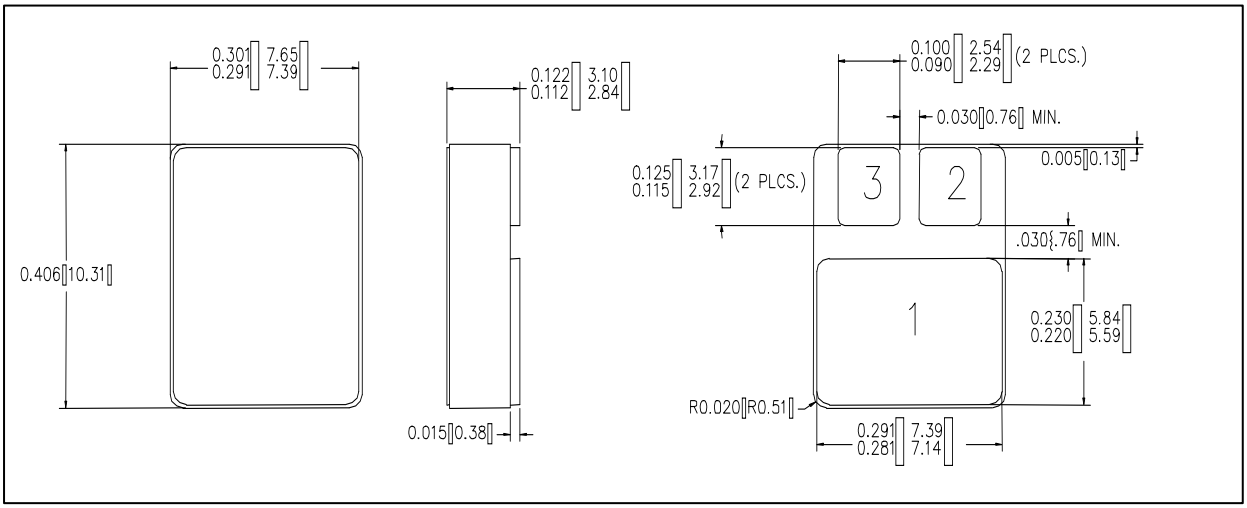
MECHANICAL DIMENSIONS: in Inches / mm



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PINOUT TABLE

N Channel Mosfet	DRAIN	GATE	SOURCE